Peter Lytvyn

List of Publications by Year in descending order

214 papers	1,819 citations	361296 20 h-index	395590 33 g-index
215 all docs	215 docs citations	215 times ranked	1990 citing authors

#	Article	IF	Citations
1	Structural, optical and magnetic properties of stencil-free printed ZnO layers doped with Fe2+ and Fe3+ ions. Materials Chemistry and Physics, 2022, 276, 125329.	2.0	3
2	Current transfer processes in a hydrated layer localized in a two-layer porous structure of nanosized ZrO2. Journal of Materials Science: Materials in Electronics, 2022, 33, 2753-2764.	1.1	3
3	Phase Formation and Physicomechanical Properties of WCâ€“Coâ€“CrB2 Composites Sintered by Vacuum Hot Pressing for Drill Tools. Journal of Superhard Materials, 2022, 44, 1-11.	0.5	1
4	Digital micro-photogrammetry in analysis and modeling habit and sectoral structure of real high-pressure high-temperature single-crystal diamonds. Review of Scientific Instruments, 2022, 93, 033903.	0.6	5
5	Influence of different aligning surfaces on the morphology of dichroic squaraine films. Polymer Bulletin, 2021, 78, 1313-1329.	1.7	3
6	Impact of low energy ion beams on the properties of rr-P3HT films. Applied Surface Science, 2021, 535, 147619.	3.1	0
7	Growth kinetics and nanoscale structure-property relationships of InN nanostructures on GaN(0Â0Â0Â1). Applied Surface Science, 2021, 537, 147997.	3.1	5
8	Impact of Surface Plasmon Polaritons on Silver Photodiffusion into As2S3 Film. Plasmonics, 2021, 16, 181-188.	1.8	8
9	Indium segregation in ultra-thin In(Ga)As/GaAs single quantum wells revealed by photoluminescence spectroscopy. Applied Physics Letters, 2021, 118, .	1.5	5
10	Structure and Mechanical Properties of Tiâ€“Alâ€“C and Tiâ€“Alâ€“Siâ€“C Films: Experimental and First-Principles Studies. Journal of Superhard Materials, 2021, 43, 100-110.	0.5	6
11	Plasma treatment as a versatile tool for tuning of sorption properties of thin nanoporous carbon films. Applied Surface Science, 2021, 544, 148876.	3.1	13
12	Growth-sector dependence of morphological, structural and optical features in boron-doped HPHT diamond crystals. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2021, 24, 261-271.	0.3	6
13	Variations of morphology of fluoropolymer thin films versus deposition conditions. Surface Topography: Metrology and Properties, 2021, 9, 045006.	0.9	1
14	Conductivity-Type Conversion in Self-Assembled GeSn Stripes on Ge/Si(100) under Electric Field. ACS Applied Electronic Materials, 2021, 3, 4388-4397.	2.0	2
15	Magnetic and optical properties of printed ZnO:Co polycrystalline layers. Materials Science in Semiconductor Processing, 2021, 135, 106054.	1.9	9
16	Structure and Properties of WCâ€“Co Composites with Different CrB2 Concentrations, Sintered by Vacuum Hot Pressing, for Drill Bits. Journal of Superhard Materials, 2021, 43, 344-354.	0.5	10
17	Shear-Induced Metallization on the (001) and (111) Faces of Diamond during Hardness Tests. Journal of Superhard Materials, 2021, 43, 379-391.	0.5	0
18	Using Digital Microphotogrammetry for Morphology Analysis of HPHT-Diamond Single Crystals. Journal of Superhard Materials, 2021, 43, 457-459.	0.5	1

#	Article	IF	Citations
19	ÐÐ°Ð¿Ñ–Ð²Ð¿Ñ€Ð¾Ð²Ñ–Ð Ð½Ð¸Ð¹ÐºÐ¾Ð²Ñ– HPHT-Ð°Ð»Ð¼Ð°Ð·Ð¸ Ñðº Ð°ÐºÑ‚Ð¸Ð²Ð½Ñ– ÐµÐ»ÐµÐ¼ÐµÐ½Ñ‚Ð¸ Ð´Ð»Ñ ÐµÐ»ÐµÐºÑ‚Ñ€Ð		
20	ELECTRONIC AND STRUCTURAL PROPERTIES OF Siâ€“Gdâ€“O ELECTRON EMITTER. Surface Review and Letters, 2020, 27, 1950089.	0.5	0
21	Investigation of structural changes in AsxSe100-x amorphous thin films after electron beam irradiation with XAFS, XANES and Kelvin force microscopy. Applied Surface Science, 2020, 530, 147266.	3.1	3
22	Graphitic Nanoporous Carbon Thin Films: Fabrication Method, Structural, Electrical and Gas Sensor Properties. ECS Transactions, 2020, 97, 151-156.	0.3	2
23	Impact of defects on photoexcited carrier relaxation dynamics in GeSn thin films. Journal of Physics Condensed Matter, 2020, 33, 065702.	0.7	6
24	Highly porous carbon films fabricated by magnetron plasma enhanced chemical vapor deposition: Structure, properties and implementation. Applied Surface Science, 2019, 496, 143735.	3.1	5
25	Investigation of undoped and Tb-doped ZnO films on Al2O3 substrate by infrared reflection method. Thin Solid Films, 2019, 673, 136-140.	0.8	9
26	Photoluminescence, conductivity and structural study of terbium doped ZnO films grown on different substrates. Materials Science in Semiconductor Processing, 2019, 94, 51-56.	1.9	12
27	Toward deposition of organic solid with controlled morphology on selected surfaces. Applied Physics A: Materials Science and Processing, 2019, 125, 1.	1.1	5
28	Plasmon-Stimulated Photodoping in the Thin-Layer As2S3â€“Ag Structure. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2019, 127, 938-942.	0.2	5
29	Local Strain and Crystalline Defects in GaN/AlGaN/GaN(0001) Heterostructures Induced by Compositionally Graded AlGaN Buried Layers. Crystal Growth and Design, 2019, 19, 200-210.	1.4	11
30	Modification of GaN thin film on sapphire substrate optical properties under weak magnetic fields. Materials Research Express, 2019, 6, 036413.	0.8	2
31	Efficient SERS substrates based on laterally ordered gold nanostructures made using interference lithography. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2019, 22, 215-223.	0.3	4
32	Effect of electron-beam treatment of sensor glass substrates for SPR devices on their metrological characteristics. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2019, 22, 444-451.	0.3	5
33	Magnetic Microstructure of Epitaxial Films of LaGa-Substituted Yttrium Iron Garnet. Metallofizika I Noveishie Tekhnologii, 2019, 41, 529-548.	0.2	2
34	Control of plasmons excitation by P- and S-polarized light in gold nanowire gratings by azimuthal angle variation. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2019, 22, 353-360.	0.3	0
35	Mechanical strain in the structure of array of silicon nanowires grown on a silicon substrate. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2019, 22, 293-298.	0.3	0
36	Polarization Effects in Graded AlGaN Nanolayers Revealed by Current-Sensing and Kelvin Probe Microscopy. ACS Applied Materials & Interfaces, 2018, 10, 6755-6763.	4.0	16

#	Article	IF	Citations
37	Kinetically controlled transition from 2D nanostructured films to 3D multifaceted InN nanocrystals on GaN(0001). CrystEngComm, 2018, 20, 1499-1508.	1.3	7
38	Sputtering effects on mirrors made of different tungsten grades. Journal of Nuclear Materials, 2018, 500, 56-63.	1.3	2
39	Selective light-induced mass transport in amorphous As x Se 100â˜'x films driven by the composition tuning: Effect of temperature on maximum acceleration. Journal of Non-Crystalline Solids, 2018, 493, 86-93.	1.5	17
40	Formation of Nanoscale Structures on Chalcogenide Films. Physica Status Solidi (B): Basic Research, 2018, 255, 1700405.	0.7	6
41	Surface potential of meso-dimensional ZnS:Mn particles obtained using SHS method. Journal of Nanoparticle Research, 2018, 20, 1.	0.8	4
42	Micro-Raman spectroscopy and electrical conductivity of graphene layer on SiO₂ dielectric subjected to electron beam irradiation. Materials Research Express, 2018, 5, 116405.	0.8	3
43	Strain relaxation in GaN/AlN superlattices on GaN(0001) substrate: Combined superlattice-to-substrate lattice misfit and thickness-dependent effects. Materials and Design, 2018, 157, 141-150.	3.3	5
44	Low-Temperature Reduction of Graphene Oxide: Electrical Conductance and Scanning Kelvin Probe Force Microscopy. Nanoscale Research Letters, 2018, 13, 139.	3.1	63
45	Formation of Nanostructures Upon Photoexcitation of Surface Plasmon Resonance in Nanocomposites Derived from Textured Gold Films and Chalcogenide Glass. Theoretical and Experimental Chemistry, 2018, 54, 107-113.	0.2	1
46	Growth of silicon self-assembled nanowires by using gold-enhanced CVD technology. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2018, 21, 282-287.	0.3	3
47	Estimation of the Relative Energy of Grain Boundaries in Silicon Films by the Grain Boundary Grooves Method. Journal of Nano- and Electronic Physics, 2018, 10, 06040-1-06040-4.	0.2	2
48	Features of mechanical scanning probe lithography on graphene oxide and As(Ge)Se chalcogenide resist. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2018, 21, 152-159.	0.3	0
49	Direct Magnetic Relief Recording Using As40S60: Mnâ€“Se Nanocomposite Multilayer Structures. Nanoscale Research Letters, 2017, 12, 286.	3.1	16
50	Raman Submicron Spatial Mapping of Individual Mn-doped ZnO Nanorods. Nanoscale Research Letters, 2017, 12, 351.	3.1	51
51	Transformation of graphene flakes into carbon nanostructures byÎ³-irradiation. Materials Research Express, 2017, 4, 045602.	0.8	1
52	Au Gratings Fabricated by Interference Lithography for Experimental Study of Localized and Propagating Surface Plasmons. Nanoscale Research Letters, 2017, 12, 190.	3.1	8
53	Effect of well/barrier thickness ratio on strain relaxation in GaN/AlN superlattices grown on GaN/sapphire template. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	0.6	5
54	Invariance of multifractal spectrums of spatial forms on the surface of ZnxCd1-xTe â€“ Si heterocompositions synthesized by electron beam epitaxy and hot wall epitaxy. Journal of Crystal Growth, 2017, 475, 144-149.	0.7	3

#	Article	IF	Citations
55	Enhanced recrystallization and dopant activation of P+ ion-implanted super-thin Ge layers by RF hydrogen plasma treatment. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	0.6	3
56	Effect of electron beam irradiation on structural and electrical properties of graphene-SiO<inf>2</inf>-Si structures. , 2017, , .		2
57	Vickers Hardness of Diamond and cBN Single Crystals: AFM Approach. Crystals, 2017, 7, 369.	1.0	36
58	The influence of substrate temperature on properties of Cu-Al-O films deposited using the reactive ion beam sputtering method. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2017, 20, 314-318.	0.3	1
59	Development of Technology for Sensor Chip Production with Increased Sensitivity and Improved Physical and Mechanical Characteristics for Optical Sensors Based on Surface Plasmon Resonance. Science and Innovation, 2017, 13, 25-33.	0.2	0
60	Hydrogen plasma modification of shallow implanted Germanium layers. , 2016, , .		0
61	Multifractal spectrums for volumes of spatial forms on surface of Zn x Cd 1â^'x Teâ€“Si (111) heterostructures and estimation of the fractal surface energy. Journal of Crystal Growth, 2016, 450, 28-33.	0.7	8
62	The Peculiarities of Strain Relaxation in GaN/AlN Superlattices Grown on Vicinal GaN (0001) Substrate: Comparative XRD and AFM Study. Nanoscale Research Letters, 2016, 11, 252.	3.1	12
63	Improved core model of indentation and its application to measure diamond hardness. Journal of Superhard Materials, 2016, 38, 289-305.	0.5	7
64	Direct Determination of 3D Distribution of Elemental Composition in Single Semiconductor Nanoislands by Scanning Auger Microscopy. Nanoscale Research Letters, 2016, 11, 103.	3.1	7
65	Formation of Nanoporous Anodic Alumina by Anodization of Aluminum Films on Glass Substrates. Nanoscale Research Letters, 2016, 11, 203.	3.1	10
66	Magnetic and structural changes in the near-surface epitaxial Y₂₉₅La₀₀₅Fe₅O₁₂ films after high-dose ion implantation. Applied Optics, 2016, 55, B144.	0.9	4
67	Precise Manipulations with Asymmetric Nano-Objects Viscoelastically Bound to a Surface. Journal of Nano Research, 2016, 39, 256-276.	0.8	1
68	Mechanisms of the degradation of Schottky-barrier photodiodes based on ZnS single crystals. Semiconductors, 2016, 50, 112-119.	0.2	3
69	Optical and structural properties of Mn-doped ZnO nanorods grown by aqueous chemical growth for spintronic applications. Thin Solid Films, 2016, 601, 22-27.	0.8	9
70	RF plasma treatment of shallow ion-implanted layers of germanium. Materials Science in Semiconductor Processing, 2016, 42, 204-209.	1.9	4
71	Microanalysis of magnetic structure of yttrium-iron garnet films by using the scanning probe microscopy methods. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2016, 19, 90-97.	0.3	1
72	Ordering of InGaAs Quantum Dots Grown by Molecular Beam Epitaxy under As2 gas flux. Materials Research Society Symposia Proceedings, 2015, 1792, 1.	0.1	0

#	Article	IF	Citations
73	The role of beneficial bacteria wall elasticity in regulating innate immune response. EPMA Journal, 2015, 6, 13.	3.3	48
74	Fabrication of Periodic Plasmonic Structures Using Interference Lithography and Chalcogenide Photoresist. Nanoscale Research Letters, 2015, 10, 497.	3.1	21
75	Preparation and optical properties of highly luminescent colloidal single-layer carbon nitride. RSC Advances, 2015, 5, 46843-46849.	1.7	24
76	Nanoscale Electrostructural Characterization of Compositionally Graded Al_xGa_{1â€“x}N Heterostructures on GaN/Sapphire (0001) Substrate. ACS Applied Materials & Interfaces, 2015, 7, 23320-23327.	4.0	17
77	Morphology of sulphur-terminated compound deposits condensed on different substrates in vacuum. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2015, 18, 433-437.	0.3	1
78	Platinum Nanoparticles with Adsorptive Layer of Chlorella vulgaris Polysaccharides Inactivate Tumor Cells of Ascitic Ehrlich Carcinoma, Ovarian Cancer and Leukemia. Springer Proceedings in Physics, 2015, , 257-268.	0.1	0
79	Temperature driven three-dimensional ordering of InGaAs/GaAs quantum dot superlattices grown under As2 gas flux. Applied Surface Science, 2014, 305, 689-696.	3.1	3
80	Electron-beam induced variation of surface profile in amorphous As20Se80 films. Journal of Applied Physics, 2014, 115, .	1.1	11
81	Effect of film growth rate and thickness on properties of Ge/GaAs(100) thin films. Thin Solid Films, 2014, 550, 715-722.	0.8	9
82	Light-induced mass transport in amorphous chalcogenides: Toward surface plasmon-assisted nanolithography and near-field nanoimaging. Physica Status Solidi (B): Basic Research, 2014, 251, 1354-1362.	0.7	25
83	Spatial distribution of free carrier concentration in vertical GaN Gunnâ€diode structures studied by confocal microâ€Raman spectroscopy and Kelvin probe force microscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 269-273.	0.8	3
84	Multifractal analysis of areas of spatial forms on surface of Zn Cd1âˆ’Teâ€“Si (111) heterocompositions. Journal of Crystal Growth, 2014, 404, 204-209.	0.7	11
85	Multifractal parameterization of space forms on surfaces of Zn x Cd1 âˆ’ x Te-Si(111) heterocompositions and its relationship to the conditions of layer synthesis. Russian Journal of Physical Chemistry A, 2014, 88, 1375-1381.	0.1	5
86	Structural transformation and functional properties of vanadium oxide films after low-temperature annealing. Thin Solid Films, 2014, 564, 179-185.	0.8	20
87	Scanning Probe Microscopy in Practical Diagnostic: 3D Topography Imaging and Nanometrology. Engineering Materials, 2014, , 179-219.	0.3	1
88	The growth of weakly coupled graphene sheets from silicon carbide powder. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2014, 17, 301-307.	0.3	2
89	Reflectometry Study of Nanoporous Films with Arrays of Gold Nanoparticles. Ukrainian Journal of Physics, 2014, 59, 915-921.	0.1	6
90	Fabrication, properties and application of Ge-on-GaAs thin nanoheterogeneous films. Tekhnologiya I Konstruirovanie V Elektronnoi Apparature, 2014, , 39-44.	0.1	0

#	Article	IF	Citations
91	Structure and mechanical properties of Ti-Al-Si-N protective coatings deposited from separated plasma of a vacuum arc. Journal of Superhard Materials, 2013, 35, 20-28.	0.5	6
92	Electron beam-induced mass transport in Asâ€“Se thin films: compositional dependence and glass network topological effects. Journal Physics D: Applied Physics, 2013, 46, 245303.	1.3	21
93	Carbon-rich nanostructured a-SiC for cold emitters. , 2013, , .		0
94	Ge/GaAs thin films for thermometer and bolometer application. , 2013, , .		0
95	Characterization of graphene layers by Kelvin probe force microscopy and microâ€Raman spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1172-1175.	0.8	13
96	Substrate-induced self-assembly of donorâ€“acceptor type compounds with terminal thiocarbonyl groups. Thin Solid Films, 2013, 539, 127-133.	0.8	6
97	Nano- and micro-scale morghological defects in oxidized a-SiC:H thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 619-623.	0.8	0
98	Graphene layers fabricated from the Ni/a-SiC bilayer precursor. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2013, 16, 322-330.	0.3	2
99	Light-induced mass transport in amorphous chalcogenides/gold nanoparticles composites. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2013, 16, 354-361.	0.3	2
100	Magnetic force microscopy of YLaFeO films implanted by high dose of nitrogen ions. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2013, 16, 246-252.	0.3	2
101	Structural study of Ge/GaAs thin films. Journal of Physics: Conference Series, 2012, 371, 012040.	0.3	7
102	Identification of nanoscale structure and morphology reconstruction in oxidized a-SiC:H thin films. Applied Surface Science, 2012, 260, 73-76.	3.1	3
103	E-beam induced mass transport in amorphous As20Se80 films. Materials Letters, 2012, 85, 113-116.	1.3	16
104	Effect of dimensionality and morphology on polarized photoluminescence in quantum dot-chain structures. Journal of Applied Physics, 2012, 112, .	1.1	10
105	Substrate effects on the strain relaxation in GaN/AlN short-period superlattices. Nanoscale Research Letters, 2012, 7, 289.	3.1	37
106	Calcein and calceinâ˜'Ag films under vapor exposure: Sensing properties and reversible film restructuring. Talanta, 2012, 101, 267-272.	2.9	3
107	Nanomechanical properties of pure and doped Ta₂O₅ and the effect of microwave irradiation. Journal Physics D: Applied Physics, 2012, 45, 475304.	1.3	15
108	Effects of the lateral ordering of self-assembled SiGe nanoislands grown on strained Si1 â˜' x Ge x buffer layers. Semiconductors, 2012, 46, 647-654.	0.2	4

#	Article	IF	Citations
109	Macro- and nanoscopic capillary effects on nanostructured real surfaces. Journal of Superhard Materials, 2012, 34, 81-94.	0.5	2
110	Mechanical scanning probe nanolithography: modeling and application. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2012, 15, 321-327.	0.3	1
111	Tailoring the electrical properties of Ge/GaAs by film deposition rate and preparation of fully compensated Ge films. Physical Review B, 2011, 84, .	1.1	9
112	Isotropic Hall effect and â€œfreeze-inâ€•of carriers in the InGaAs self-assembled quantum wires. Journal of Applied Physics, 2011, 110, .	1.1	14
113	Conducting and topographic AFM analysis of Hf-doped and Al-doped Ta2O5 films. Thin Solid Films, 2011, 519, 8182-8190.	0.8	6
114	Alignment and optical polarization of InGaAs quantum wires on GaAs high index surfaces. Materials Letters, 2011, 65, 1427-1430.	1.3	3
115	Photoinduced mass-transport based holographic recording of surface relief gratings in amorphous selenium films. Applied Physics Letters, 2011, 99, 051906.	1.5	39
116	Influence of template type and buffer strain on structural properties of GaN multilayer quantum wells grown by PAMBE, an x-ray study. Journal Physics D: Applied Physics, 2011, 44, 025403.	1.3	12
117	Scanning confocal Raman spectroscopy of silicon phase distribution in individual Si nanowires. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1012-1016.	0.8	6
118	Laser oscillation in Cr2+ :ZnS waveguide thin-film structures under electrical pumping with impact excitation mechanism. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2011, 14, 339-343.	0.3	3
119	Radiation effects and interphase interactions in ohmic and barrier contacts to indium phosphide as induced by rapid thermal annealing and irradiation with Î³-ray 60Co photons. Semiconductors, 2010, 44, 1559-1566.	0.2	2
120	Comparative studies of mechanical properties of stishovite and sapphire single crystals by nanoindentation. Journal of Superhard Materials, 2010, 32, 406-414.	0.5	26
121	Synthesis and properties of porous SiC ceramics. Journal of Applied Physics, 2010, 107, .	1.1	15
122	Bright emission from amorphous sicn thin films. , 2010, , .		0
123	Interface roughness scattering in laterally coupled InGaAs quantum wires. Applied Physics Letters, 2010, 97, 262103.	1.5	14
124	Gigantic uphill diffusion during self-assembled growth of Ge quantum dots on strained SiGe sublayers. Applied Physics Letters, 2010, 96, .	1.5	19
125	Alternating matter motion in photoinduced mass transport driven and enhanced by light polarization in amorphous chalcogenide films. Applied Physics Letters, 2010, 97, 031905.	1.5	35
126	Giant enhancement of elastic surface plasmon-polariton scattering. Optics Express, 2010, 18, 43.	1.7	7

#	Article	IF	Citations
127	Real-time atomic force microscopy imaging of photoinduced surface deformation in AsxSe100â^'x chalcogenide films. Applied Physics Letters, 2010, 96, 111908.	1.5	45
128	Direct surface relief formation in As-S(Se) layers. Proceedings of SPIE, 2010, , .	0.8	4
129	Nanoprobe spectroscopy of capillary forces and its application for a real surface diagnostics. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2010, 13, 111-124.	0.3	3
130	On the complex behavior of strain relaxation in (In,Ga)As/GaAs(001) quantum dot molecules. Applied Physics Letters, 2009, 95, 023103.	1.5	1
131	Conductive-atomic force microscopy characterization of Ta₂O₅/SiO₂stacks and the effect of microwave irradiation. Journal Physics D: Applied Physics, 2009, 42, 145301.	1.3	6
132	One-dimensional features of In(Ga)As/GaAs dot chain structures with changeable interdot coupling. New Journal of Physics, 2009, 11, 043022.	1.2	13
133	Threeâ€dimensional ordering in selfâ€organized (In,Ga)As quantum dot multilayer structures. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1748-1751.	0.8	5
134	Au-TiB x -n-6H-SiC Schottky barrier diodes: Specific features of charge transport in rectifying and nonrectifying contacts. Semiconductors, 2009, 43, 865-871.	0.2	20
135	Surface morphology of as-deposited and illuminated Asâ€“Se chalcogenide thin films. Journal of Non-Crystalline Solids, 2009, 355, 1993-1997.	1.5	36
136	Diluted magnetic semiconductors based on IIâ€“VI, IIIâ€“VI, and IVâ€“VI compounds. Low Temperature Physics, 2009, 35, 62-70.	0.2	9
137	Ultrasonic assisted nanomanipulations with atomic force microscope. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2009, 13, 036-042.	0.3	6
138	Observation of unique blister-like surface features on amorphous metallic alloys following bombardment with deuterium ions. Journal of Nuclear Materials, 2008, 376, 125-127.	1.3	12
139	Properties of barrier contacts with nanosize TiB x layers to InP. Semiconductors, 2008, 42, 777-782.	0.2	1
140	Room Temperature Near-Infrared Photoresponse Based on Interband Transitions in $hbox{In}_{0.35}hbox{Ga}_{0.65}hbox{As}$ Multiple Quantum Dot Photodetector. IEEE Electron Device Letters, 2008, 29, 224-227.	2.2	25
141	Deep traps in GaAs/InGaAs quantum wells and quantum dots, studied by noise spectroscopy. Journal of Applied Physics, 2008, 104, 103709.	1.1	16
142	Engineering of 3D self-directed quantum dot ordering in multilayer InGaAs/GaAs nanostructures by means of flux gas composition. Nanotechnology, 2008, 19, 505605.	1.3	5
143	Broadband photoresponse from InAs quantum dots embedded in a graded well for visible to mid-infrared detection. Proceedings of SPIE, 2008, , .	0.8	0
144	Screen-printed p-CdTe layers for CdS/CdTe solar cells. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2008, 8, 61-65.	0.3	2

#	Article	IF	Citations
145	Initial stages of chain formation in a single layer of (In,Ga)As quantum dots grown on GaAs (100). Applied Physics Letters, 2007, 91, .	1.5	13
146	Multi-color Photoresponse Based on Interband and Intersubband Transitions in InAs and InGaAs Quantum Dot Photodetectors. Materials Research Society Symposia Proceedings, 2007, 1055, 2.	0.1	0
147	Two-dimensional ordering of (In,Ga)As quantum dots in vertical multilayers grown on GaAs(100) and (n11). Applied Physics Letters, 2007, 91, .	1.5	15
148	Influence of plasma discharge on the structure of polytetrafluoroethylene film and step coverage on polymer substrate. Materials Science and Engineering C, 2007, 27, 1227-1231.	3.8	17
149	Quantized field-electron emission at 300K in self-assembled arrays of silicon nanowires. Physica E: Low-Dimensional Systems and Nanostructures, 2007, 37, 212-217.	1.3	3
150	Lateral ordering of quantum dots and wires in the (In,Ga)As/GaAs(100) multilayer structures. Semiconductors, 2007, 41, 73-80.	0.2	5
151	The correlation between the surface-energy minima and the shape of self-induced SiGe nanoislands. Semiconductors, 2006, 40, 385-390.	0.2	0
152	CdSe nanoparticles grown with different chelates. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2006, 9, 75-79.	0.3	12
153	A silicon carbide thermistor. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2006, 9, 67-70.	0.3	4
154	Oxidation of hydrogenated crystalline silicon as an alternative approach for ultrathin SiO2growth. Journal of Physics: Conference Series, 2005, 10, 246-250.	0.3	0
155	<title>Formation of nanohills on the surface of 6<emph type="1">H</emph>-SiC:N at an early stage of laser ablation</title>. , 2005, , .		0
156	Microsize defects in InGaAs/GaAs A/B multilayers quantum dot stacks. Journal of Crystal Growth, 2005, 284, 47-56.	0.7	5
157	Laser processing and characterization of ZnSâ€“Cu thin films. Applied Surface Science, 2005, 247, 434-439.	3.1	11
158	Self-Organization of Three-Dimensional Lead Telluride Nanoislands under Conditions Close to Thermodynamic Equilibrium. Technical Physics Letters, 2005, 31, 716.	0.2	3
159	Thermal stability of multilayer contacts on gallium nitride. Technical Physics Letters, 2005, 31, 1078-1081.	0.2	2
160	Electrolytic molybdenum oxides in lithium batteries. Journal of Solid State Electrochemistry, 2005, 9, 96-105.	1.2	38
161	Changes of Surface Properties of Yeast Cell Wall Under Exposure of Electromagnetic Field (40.68) Tj ETQq1 1 0.784314 rgBT /Overlock	0.7	5
162	Effect of surface energy minima on the shape of self-induced SiGe nanoislands. Physica Status Solidi (B): Basic Research, 2005, 242, 2833-2837.	0.7	1

#	Article	IF	Citations
163	Phase Transition on Surface of IV Group Semiconductors by Laser Radiation. Solid State Phenomena, 2005, 108-109, 345-350.	0.3	4
164	Title is missing!. Ukrainian Journal of Physical Optics, 2005, 6, 78-86.	9.7	0
165	Dynamic of Laser Ablation in SiC. Materials Science Forum, 2004, 457-460, 411-414.	0.3	13
166	Correlation between the energy of SiGe nanoislands and their shape and size. Physics of the Solid State, 2004, 46, 67-70.	0.2	0
167	Composition and elastic stresses in multilayer structures with Si1âˆ'x Gex nanoislands. Physics of the Solid State, 2004, 46, 85-88.	0.2	1
168	Interphase interactions and features of structural relaxation in TiBx-n-GaAs (InP, GaP, 6H-SiC) contacts subjected to active treatment. Semiconductors, 2004, 38, 737-741.	0.2	6
169	Spectral Characteristics and Surface Morphology of Organic Polymer Films Containing Vanadium Pentoxide Nanoparticles. Russian Journal of Electrochemistry, 2004, 40, 259-266.	0.3	3
170	Electrolytic Iron Sulfide Products in Lithium Batteries. Russian Journal of Electrochemistry, 2004, 40, 736-742.	0.3	2
171	Formation of rocking curves for quasi-forbidden reflections in short-periodic superlattices GaAs/AlGaAs. Journal of Applied Crystallography, 2004, 37, 150-155.	1.9	2
172	Zinc oxide - analogue of GaN with new perspective possibilities. Crystal Research and Technology, 2004, 39, 980-992.	0.6	142
173	Persistence of (In,Ga)As quantum-dot chains under index deviation from GaAs(100). Applied Physics Letters, 2004, 84, 4681-4683.	1.5	15
174	Theoretical and experimental investigations of single- and multilayer structures with SiGe nanoislands. Materials Science and Engineering C, 2003, 23, 1027-1031.	3.8	14
175	Nanocomposite Si/Diamond Layers: Room Temperature Visible-Light Emitting Systems. Chemical Vapor Deposition, 2003, 9, 139-143.	1.4	2
176	Field and photo-field electron emission from self-assembled Geâ€“Si nanostructures with quantum dots. Progress in Surface Science, 2003, 74, 305-318.	3.8	19
177	Formation of nanostructures on surface of SiC by laser radiation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 101, 155-158.	1.7	3
178	Self formation of Si nanostructured layer at the metal silicide/silicon interface. Materials Science and Engineering C, 2003, 23, 181-186.	3.8	4
179	Formation of nanostructure on surface of SiC by laser radiation. Physica Status Solidi A, 2003, 195, 199-203.	1.7	4
180	Structural-phase transformations in SiOx films in the course of vacuum heat treatment. Semiconductors, 2003, 37, 97-102.	0.2	28

#	Article	IF	Citations
181	Peculiarities of the formation and thermal stability of barrier contacts in high-sensitivity silicon carbide detector diodes. Technical Physics Letters, 2003, 29, 22-25.	0.2	4
182	Special features of formation and characteristics of Ni/21R-SiC Schottky diodes. Semiconductors, 2003, 37, 456-461.	0.2	1
183	Effect of microwave annealing on silicon dioxide/silicon carbide structures. Technical Physics, 2003, 48, 598-601.	0.2	8
184	Phase and structural changes stimulated in multilayer contacts to n-GaAs by rapid thermal annealing. Semiconductors, 2003, 37, 1114-1118.	0.2	3
185	Fabrication and cathodoluminescent properties of the ZnO-Cu,Ga and ZnS-Cu,Ga film phosphors. Journal of the Society for Information Display, 2003, 11, 21.	0.8	1
186	Laser Assisted Formation of SiC Nano-Tips for Field Emission Application. Solid State Phenomena, 2003, 94, 145-150.	0.3	1
187	Nanostructure Formation on a Surface of 6H-SiC by Laser Radiation. Materials Science Forum, 2003, 433-436, 595-598.	0.3	0
188	<title>Nanostructures formation on surface of 6H-SiC by N<formula><inf><roman>2</roman></inf></formula> laser radiation</title>. , 2003, , .		0
189	Nanostructures for formation on surface of 6H-SiC by laser radiation. , 2003, , .		0
190	Barrier Material Improvement in AlGaN/GaN Microwave Transistors Under Gamma Irradiation Treatment. Materials Research Society Symposia Proceedings, 2003, 764, 1.	0.1	3
191	Effect of Rapid Thermal Annealing Conditions on Parameters of Ni/21R-SiC Contacts. Materials Science Forum, 2002, 389-393, 905-908.	0.3	2
192	<title>Complex nanostructured silicon wire</title>. , 2002, 4806, 323.		0
193	Microscopic and optical investigation of Ge nanoislands on silicon substrates. Nanotechnology, 2002, 13, 81-85.	1.3	44
194	Near/Far-Field Investigations of the Interaction between Surface Waves and Nanoparticles. Physica Status Solidi (B): Basic Research, 2002, 229, 1283-1294.	0.7	8
195	DNA nanotechnology of carbon nanotube cells: physico-chemical models of self-organization and properties. Materials Science and Engineering C, 2002, 19, 41-45.	3.8	43
196	Microwave-stimulated relaxation of internal strains in GaAs-based device heterostructures. Technical Physics Letters, 2002, 28, 154-156.	0.2	10
197	Chemically produced ZnS: Cu films: Structure, properties, and mechanism of electroluminescence. Technical Physics, 2002, 47, 978-982.	0.2	5
198	AFM surface imaging of thermally oxidized hydrogenated crystalline silicon. Applied Surface Science, 2002, 191, 148-152.	3.1	7

#	Article	IF	Citations
199	Electrolytic Synthesis of Binary Oxide Systems Based on Manganese(II) Oxide. Russian Journal of Applied Chemistry, 2002, 75, 213-218.	0.1	2
200	Joint Electrolytic Deposition of Vanadium and Manganese Oxides. Russian Journal of Applied Chemistry, 2002, 75, 552-557.	0.1	1
201	Electrolytic Deposition of Cobalt(III) Oxide in the Presence of Nickel(II) and Chromium(III) Ions. Russian Journal of Applied Chemistry, 2002, 75, 905-910.	0.1	1
202	Peculiarities Of Th.Terrestris Spores Surface Ultrastructure Investigated By Afm. , 2002, , 341-346.		0
203	Electrolytic Preparation of Vanadium(V) Oxide from Saturated Solutions of Ammonium Metavanadate. Russian Journal of Applied Chemistry, 2001, 74, 1474-1478.	0.1	2
204	The influence of TiB2-thin film thickness on metalâ€“GaAs structural characteristics. Thin Solid Films, 2000, 373, 79-83.	0.8	8
205	On the nature of transition layer and heat tolerance of TiBx/GaAs-based contacts. Applied Surface Science, 2000, 166, 520-525.	3.1	2
206	Luminescent ZnS:Cu films prepared by chemical methods. Semiconductors, 2000, 34, 1128-1132.	0.2	18
207	Relaxation processes in Auâ€“TiB2/GaAs structures under short-term thermal annealing. Applied Surface Science, 2000, 166, 130-136.	3.1	0
208	Photoluminescence investigation of Dy incorporation into InP during liquid phase epitaxy. , 1998, 3359, 197.		0
209	<title>Liquid phase epitaxial III-V technology for photodetectors manufacturing</title>. , 1997, 3182, 146.		0
210	Heat-resistant Au-ZrB/sub x/-n-SiC 6H Schottky barriers. , 0, , .		0
211	Influence of rapid thermal annealing modes on the parameters of Ni/21R-SiC contacts. , 0, , .		0
212	Interactions between phases and thermal stability of TiB/sub x/(ZrB/sub x/)-n-SiC 6H contacts. , 0, , .		0
213	Carbon-Rich Nanostructurated a-SiC on Si Heterostructures for Field-Effect Electron Emission. Advanced Materials Research, 0, 854, 59-67.	0.3	0
214	Defect engineering using microwave processing in SiC and GaAs. Semiconductor Science and Technology, 0, , .	1.0	0